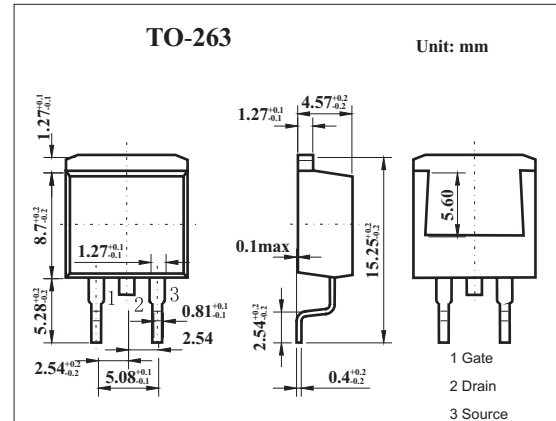


MOS Field Effect Transistor 2SK3305

■ Features

- Low gate charge
Q_G = 13 nC TYP. (V_{DD} = 400V, V_{GS} = 10 V, I_D = 5.0A)
- Gate voltage rating ±30 V
- Low on-state resistance
R_{DS(on)} = 1.5 Ω MAX. (V_{GS} = 10 V, I_D = 2.5A)
- Avalanche capability ratings



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V _{DSS}	500	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	±5	A
	I _{DP} *	±20	A
Power dissipation	P _D	T _C =25°C	75
		T _A =25°C	1.5
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10 μs, Duty Cycle ≤ 1%

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit	
Drain cut-off current	I _{DSS}	V _{DS} =500V, V _{GS} =0			100	μA	
Gate leakage current	I _{GSS}	V _{GS} =±30V, V _{DS} =0			±100	μA	
Gate cutoff voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	2.5		3.5	V	
Forward transfer admittance	Y _{fs}	V _{DS} =10V, I _D =2.5A	1.0	3.0		S	
Drain to source on-state resistance	R _{DS(on)}	V _{GS} =10V, I _D =2.5A		1.3	1.5	Ω	
Input capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0, f=1MHz		700		pF	
Output capacitance	C _{oss}				115		pF
Reverse transfer capacitance	C _{rss}				6		pF
Turn-on delay time	t _{on}	I _D =2.5A, V _{GS(on)} =10V, R _G =10Ω, V _{DD} =150V, R _L =60Ω		16		ns	
Rise time	t _r				3		ns
Turn-off delay time	t _{off}				33		ns
Fall time	t _f				5.5		ns